

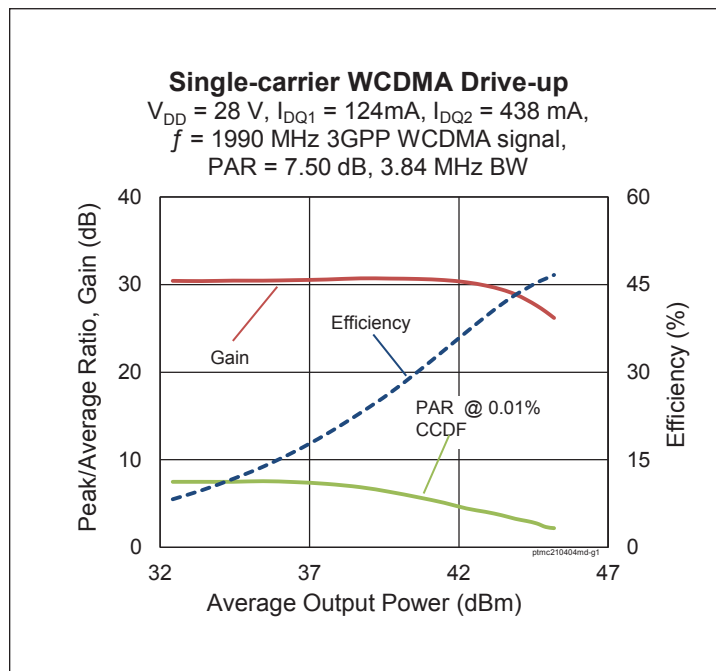
Wideband LDMOS Two-stage Integrated Power Amplifier 2 x 20 W, 28 V, 1805 – 2200 MHz

Description

The PTMC210204MD is a wideband, two-stage LDMOS integrated amplifier intended for wideband driver applications. It has internal matching for operation from 1805 to 2200 MHz. It features on-chip matching high efficiency, and dual independent outputs with 20 W of output power each. It is available in a 14-lead plastic overmold package with gull wing leads.



Package PG-HB1DSO-14-1
(formed leads)



Features

- On-chip matching for broadband operation
- Typical pulsed CW performance, 1990 MHz, 28 V, combined outputs
 - Output power at $P_{1dB} = 37\text{ W}$
 - Linear Gain = 31.5 dB
 - Efficiency = 53.1%
- Capable of handling 10:1 VSWR @ 28 V, 37 W (CW) output power
- Integrated ESD protection
- Human Body Model Class 1B (per ANSI/ESDA/ JEDEC JS-001)
- Integrated temperature compensation
- Pb-free and RoHS compliant

RF Characteristics

Single-carrier WCDMA Specifications (tested in Infineon production test fixture)

$V_{DD} = 28\text{ V}$, $I_{DQ1(A+B)} = 63\text{ mA}$, $I_{DQ2(A+B)} = 219\text{ mA}$, $P_{OUT} = 5\text{ W avg}$, $f = 1990\text{ MHz}$, 3GPP WCDMA signal, channel bandwidth = 3.84 MHz, peak/average = 7.5 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Linear Gain	G_{ps}	29	30	—	dB
Power Added Efficiency	PAE	17.5	18.5	—	%
Adjacent Channel Power Ratio	ACPR	—	-49.5	-47.5	dBc
Output PAR @ 0.01% CCDF	OPAR	7.0	7.2	—	dB

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

DC Characteristics

Stage 1	Conditions	Symbol	Min	Typ	Max	Unit
Drain Leakage Current	$V_{DS} = 28\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	0.1	μA
	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1	μA
Gate Leakage Current	$V_{GS} = 1\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	—	—	0.1	μA
On-state Resistance	$V_{GS} = 10\text{ V}, V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	1.5	—	Ω
Operating Gate Voltage	$V_{DS} = 28\text{ V}, I_{DQ1} = 63\text{ mA}$	V_{GS1}	—	2.7	—	V
Fixture Operating Gate Voltage	$V_{DS} = 28\text{ V}, I_{DQ1} = 63\text{ mA}$	V_{GS1}	—	4.9	—	V

Stage 2	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 10\text{ mA}$	$V_{BR(DSS)}$	64	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	0.1	μA
	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1	μA
Gate Leakage Current	$V_{GS} = 1\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	—	—	0.1	μA
On-state Resistance	$V_{GS} = 10\text{ V}, V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	1.5	—	Ω
Operating Gate Voltage	$V_{DS} = 28\text{ V}, I_{DQ2} = 219\text{ mA}$	V_{GS2}	—	2.7	—	V
Fixture Operating Gate Voltage	$V_{DS} = 28\text{ V}, I_{DQ2} = 219\text{ mA}$	V_{GS2}	—	4.9	—	V

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	V
Gate-Source Voltage	V_{GS}	-6 to +10	V
Junction Temperature	T_J	225	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^{\circ}\text{C}$
Operating Voltage	V_{DD}	0 to 32	V

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Thermal Resistance	Stage 1 ($T_{CASE} = 70^{\circ}\text{C}, 37\text{ W CW}$)	$R_{\theta JC}$	6.7	$^{\circ}\text{C/W}$
	Stage 2 ($T_{CASE} = 70^{\circ}\text{C}, 37\text{ W CW}$)	$R_{\theta JC}$	1.4	$^{\circ}\text{C/W}$

Moisture Sensitivity Level

Level	Test Standard	Package Temperature	Unit
3	IPC/JEDEC J-STD-020	260	$^{\circ}\text{C}$

Ordering Information

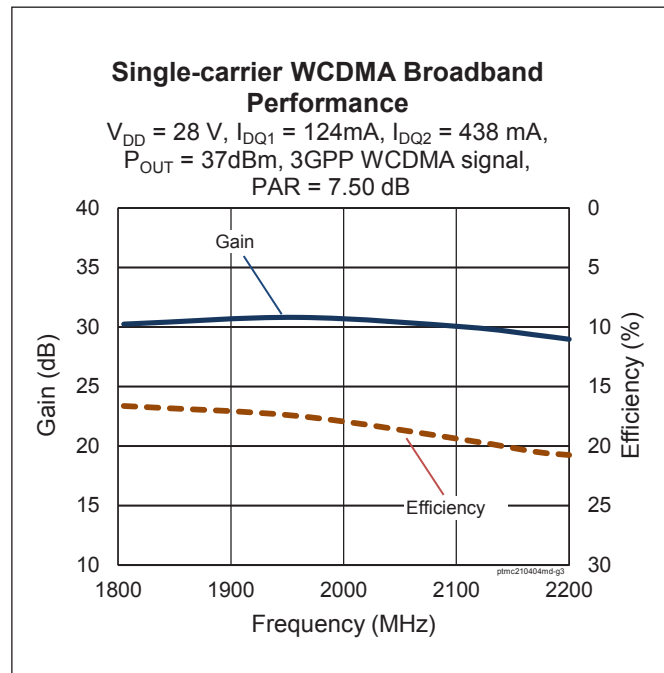
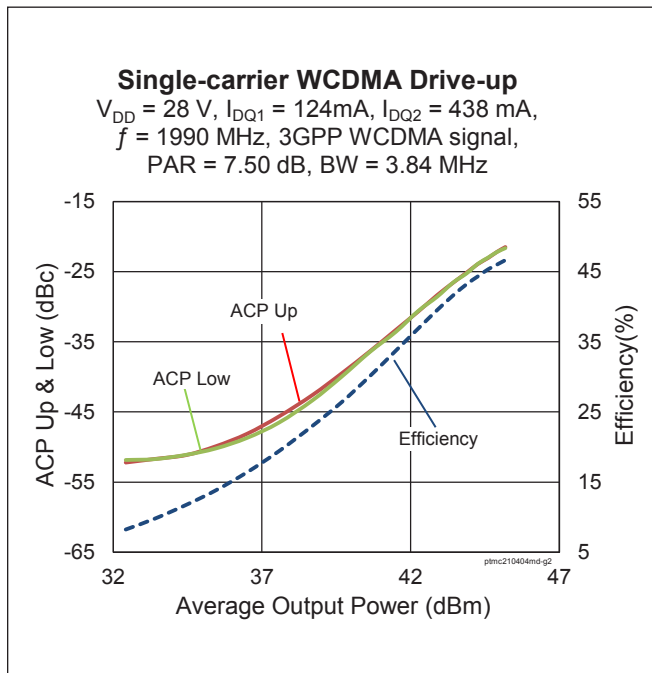
Type and Version	Order Code	Package and Description	Shipping
PTMC210404MD V1 R5	PTMC210404MDV1R5XUMA1	PG-HB1DSO-14-1, 14-lead, overmold	Tape & Reel, 500 pcs

Evaluation Boards

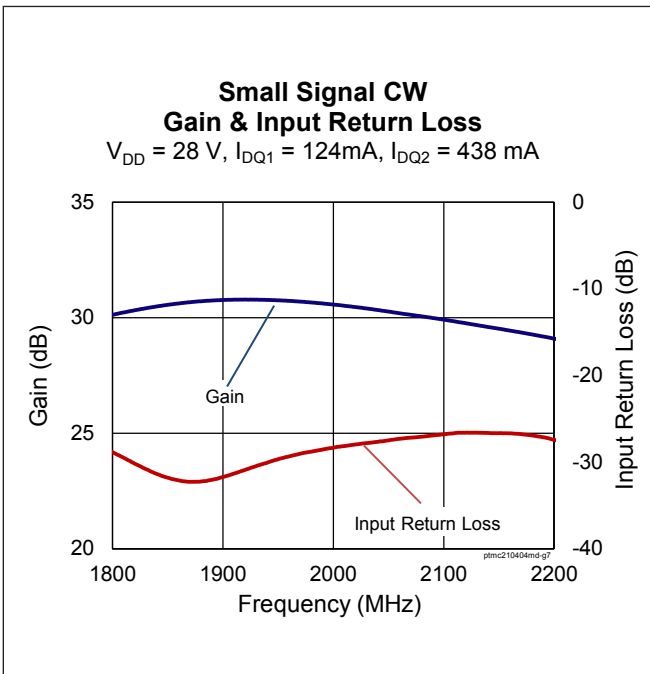
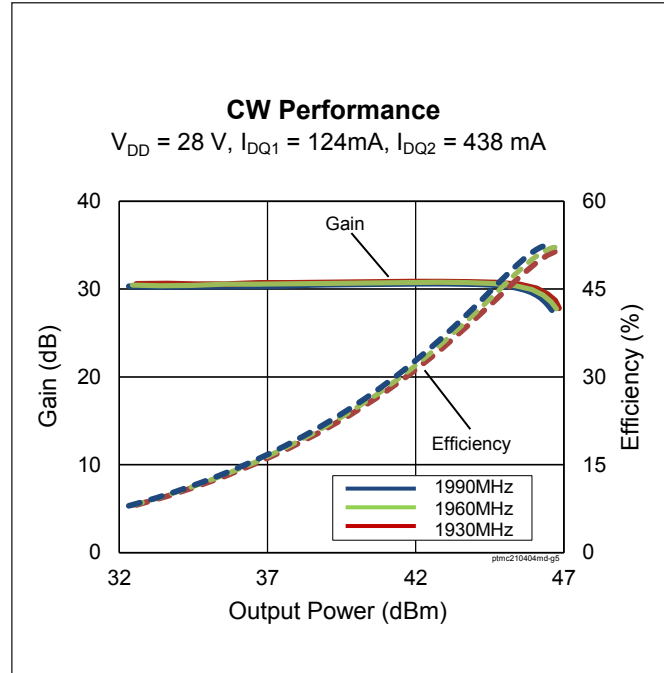
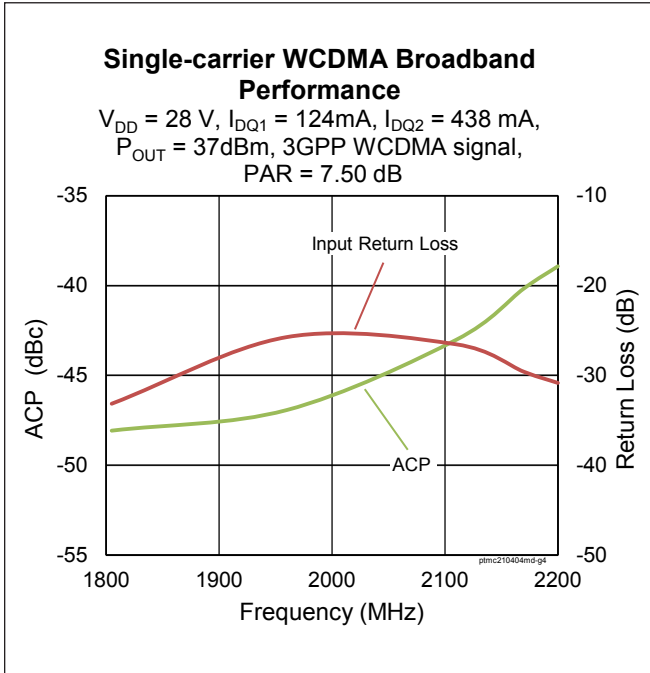
Order Code	Frequency	Description
LTN/PTMC210404MD V1	1805 – 2200 MHz	Class AB with combined outputs, R04350, 0.508 mm thick

Find Gerber files for these reference fixtures on the Infineon Web site at www.infineon.com/rfpower

Typical RF Performance (data taken in production test fixture)



Typical Performance (cont.)

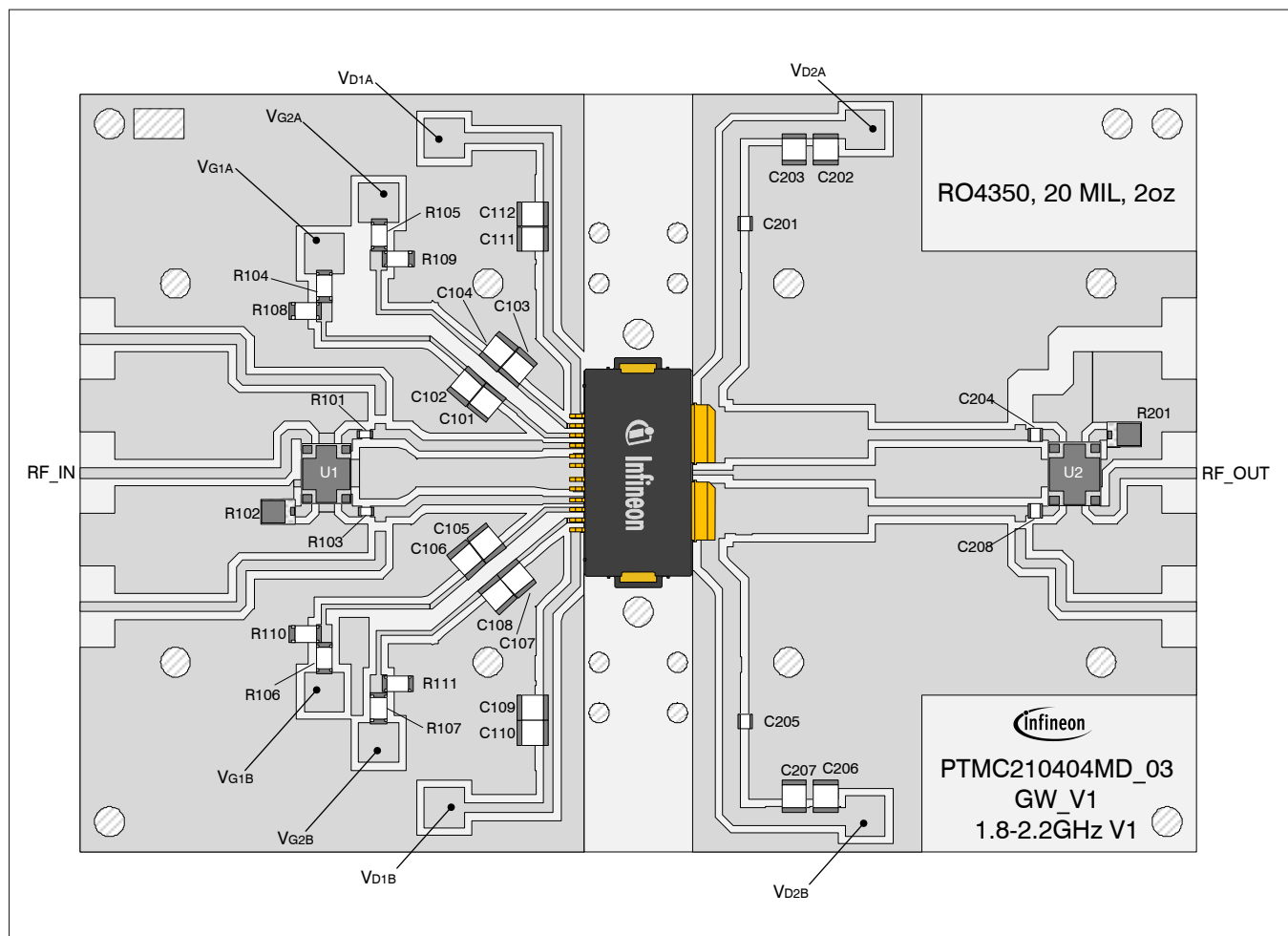


Load Pull Performance

Load Pull Performance – Pulsed CW signal: $V_{DD} = 28\text{ V}$, $I_{DQ1} = 63\text{ mA}$, $I_{DQ2} = 219\text{ mA}$, class AB, each side.

Freq [MHz]	Zs [Ω]	P _{1dB}									
		Max Output Power					Max Drain Efficiency				
		ZI [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]	ZI [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]
1805	49.8+j2.3	8.8-j6.30	29.8	43.8	23.8	51.2	13.4-j3.7	31.0	42.9	19.4	55.9
1960	49.9-j0.1	8.5-j8.20	29.5	43.8	23.9	50.5	10.9-j2.4	31.0	42.7	18.5	57.0
2170	51.9+j0.2	7.4-j7.60	27.9	43.9	24.3	51.8	7.10-j3.8	29.0	42.9	19.6	56.6
2200	49.3+j1.0	7.7-j7.70	27.6	43.8	23.8	51.5	6.90-j3.7	28.8	42.8	19.0	56.6

Reference Circuit, 1805 – 2200 MHz



Reference circuit assembly diagram (not to scale)

Reference Circuit (cont.)

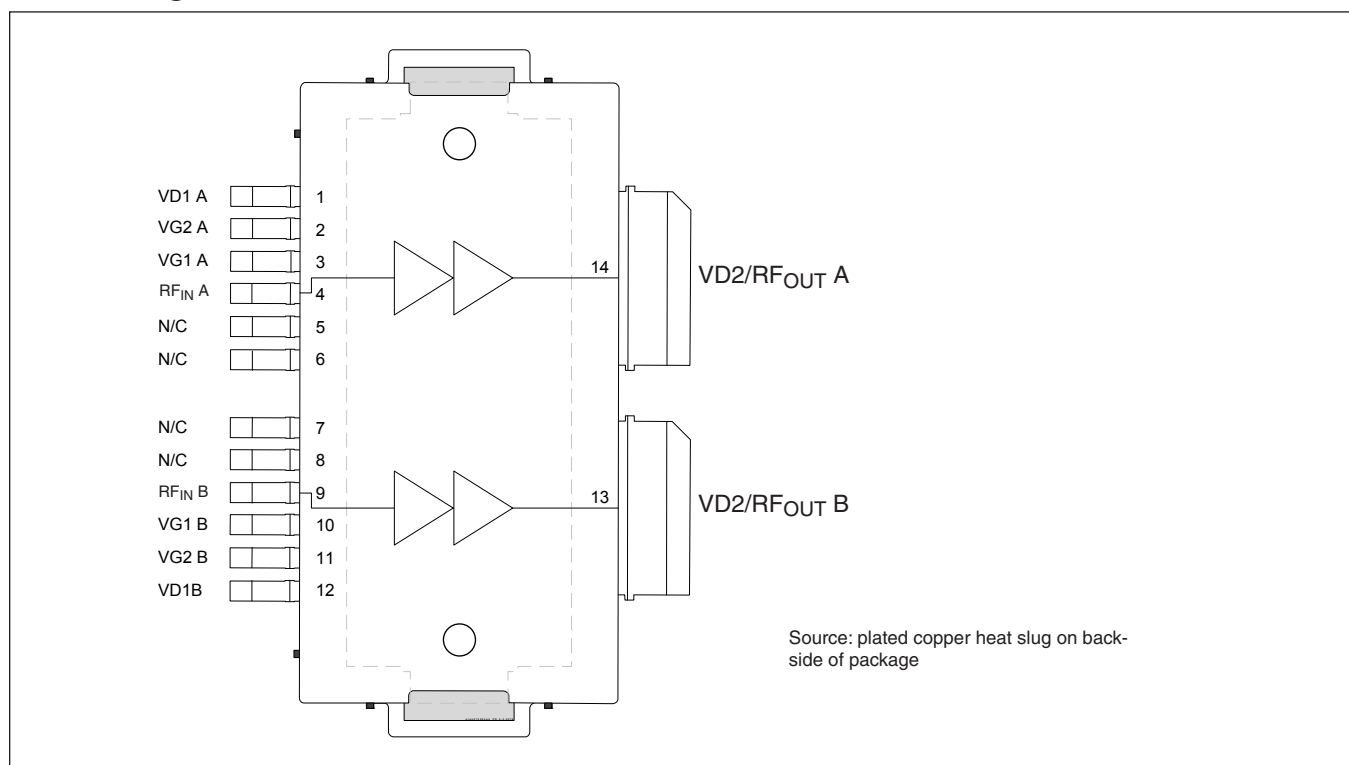
Reference Circuit Assembly

DUT	PTMC210404MD V1
Test Fixture Part No.	LTN/PTMC210404MD V1
PCB	Rogers 4350B, 0.508 mm [0.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$, $f = 1805 - 2200$ MHz
Find Gerber files for this test fixture on the Infineon Web site at http://www.infineon.com/rfpower	

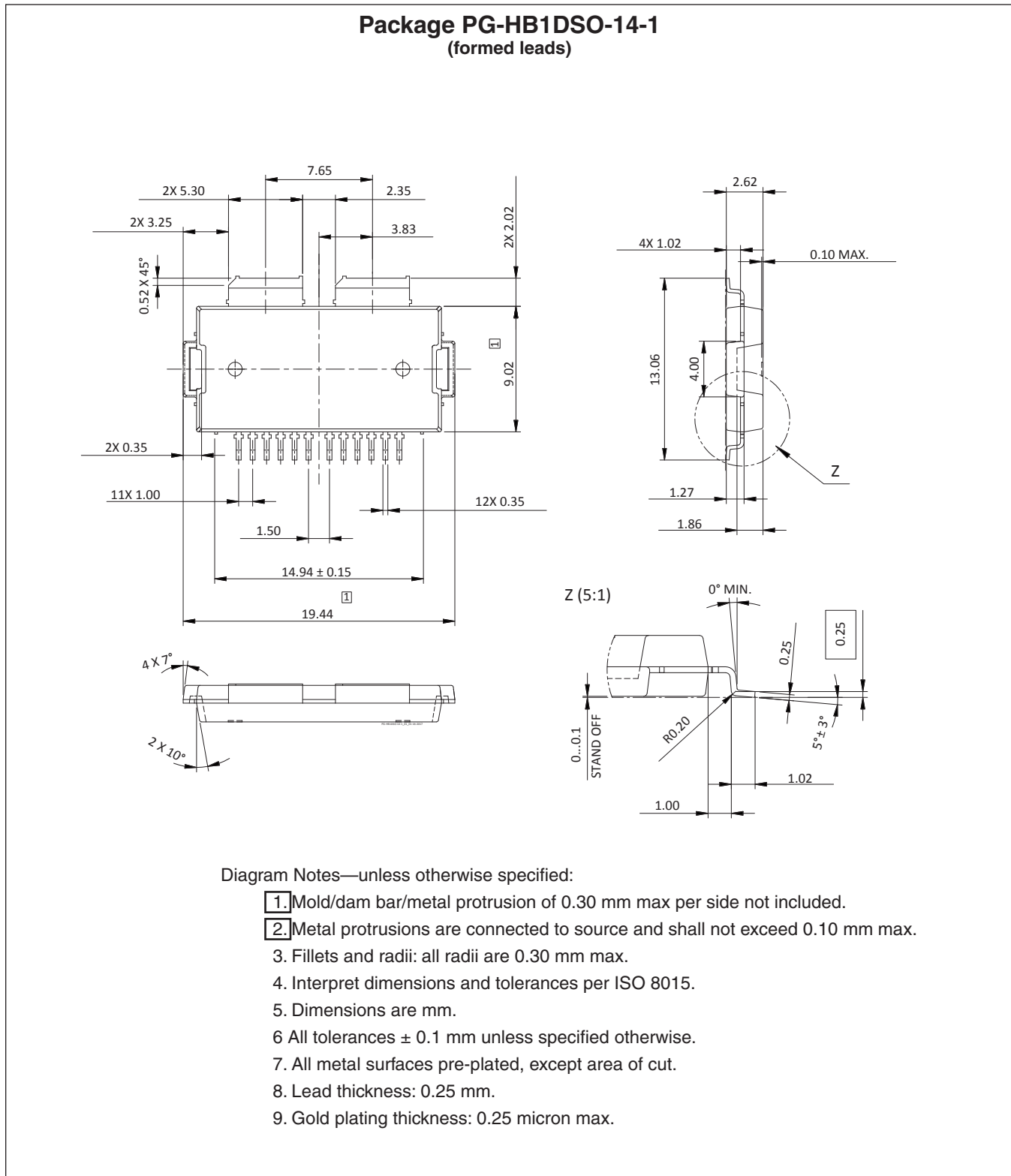
Components Information

Component	Description	Manufacturer	P/N
Input			
C101, C103, C105, C107, C109, C111, C203, C207	Capacitor, 4.7 μ F	Murata Electronics North America	GRM32ER71H475KA88L
C102, C104, C106, C108, C110, C112, C202, C206	Capacitor, 10 μ F	Taiyo Yuden	UMK325C7106MM-T
C201, C204, C205, C208	Capacitor, 10 pF	ATC	ATC800A100JT250T
R101, R103	Resistor, 0.0 ohms	Panasonic Electronic Components	ERJ-3GEY0R00V
R102, R201	Resistor, 50 ohms	ANAREN	C8A50Z4A
R104, R105, R106, R107	Resistor, 1K ohms	Panasonic Electronic Components	ERJ-8GEYJ102V
R108, R109, R110, R111	Resistor, 4.3K ohms	Panasonic Electronic Components	ERJ-8GEYJ432V
U1, U2	Hybrid Coupler	ANAREN	X3C21P1-03S

Pinout Diagram



Package Outline Specifications



Package Outline Specifications (cont.)

Package PG-HB1DSO-14-1
(formed leads, bottom side)

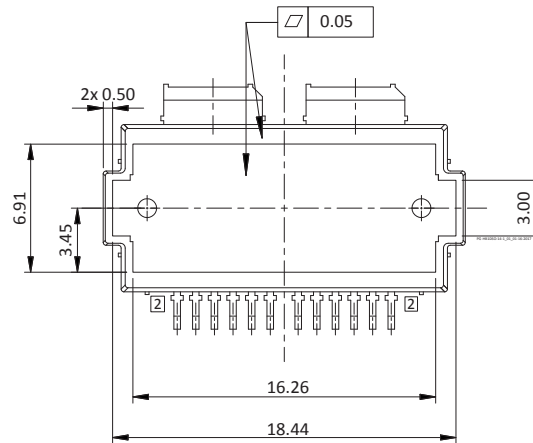


Diagram Notes—unless otherwise specified:

1. Mold/dam bar/metal protrusion of 0.30 mm max per side not included.
2. Metal protrusions are connected to source and shall not exceed 0.10 mm max.
3. Fillets and radii: all radii are 0.30 mm max.
4. Interpret dimensions and tolerances per ISO 8015.
5. Dimensions are mm.
6. All tolerances ± 0.1 mm unless specified otherwise.
7. All metal surfaces pre-plated, except area of cut.
8. Lead thickness: 0.25 mm.
9. Gold plating thickness: 0.25 micron max.

Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

Revision History

Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2017-01-20	Advance	All	Target specifications for proposed product.
02	2017-05-11	Production	All	Data Sheet reflects released product specification

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